



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

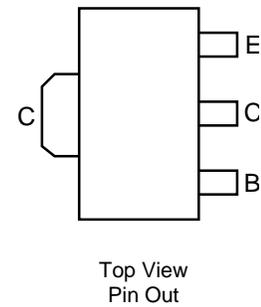
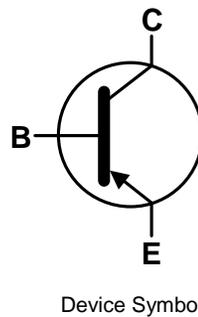
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Features

- $BV_{CEO} > -400V$
- $I_C = -200mA$ High Continuous Current
- $I_{CM} = -500mA$ Peak Pulse Current
- Excellent h_{FE} Characteristics up to $-100mA$
- Low Saturation Voltage $V_{CE(sat)} < -200mV @ -20mA$
- Complementary NPN Type: NK-FCX458

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.05 grams (Approximate)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-200	mA
Peak Pulse Current	I _{CM}	-500	mA

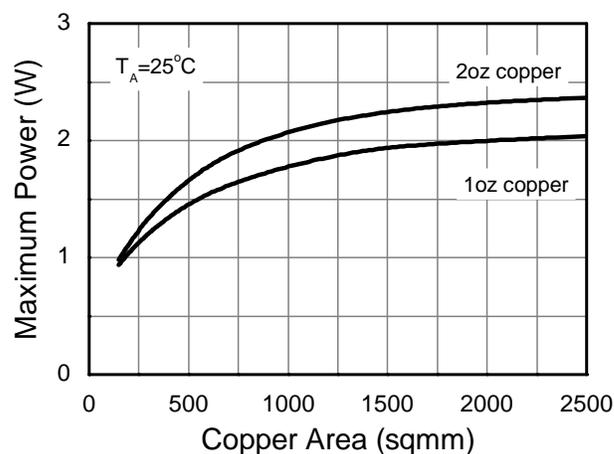
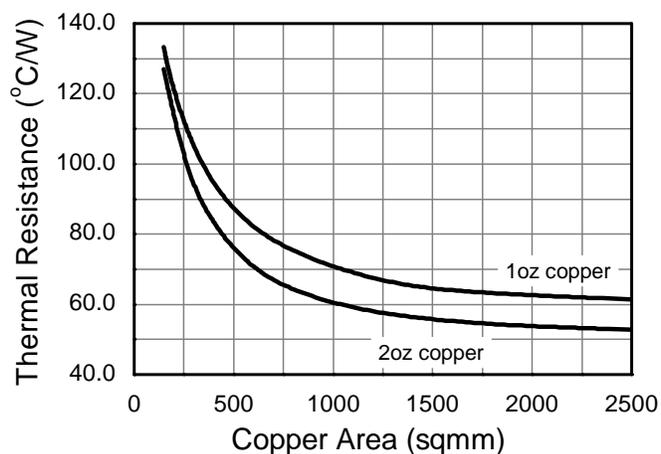
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 6)	0.7
		(Note 7)	1.0
		(Note 8)	1.5
		(Note 9)	2.0
Thermal Resistance, Junction to Ambient Air	R _{θJA}	(Note 6)	178
		(Note 7)	125
		(Note 8)	83
		(Note 9)	60
Thermal Resistance, Junction to Lead	R _{θJL}	22	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

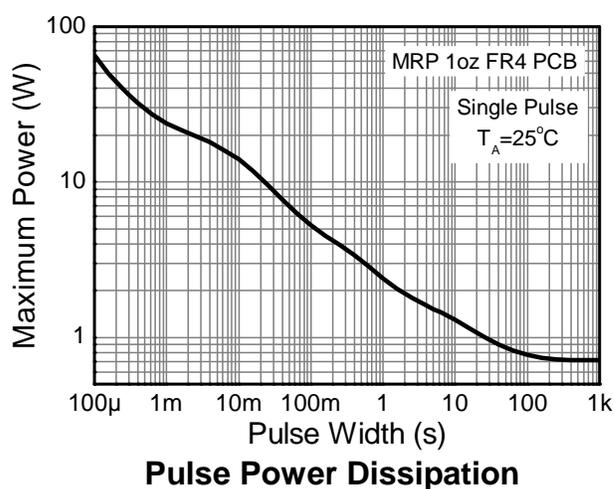
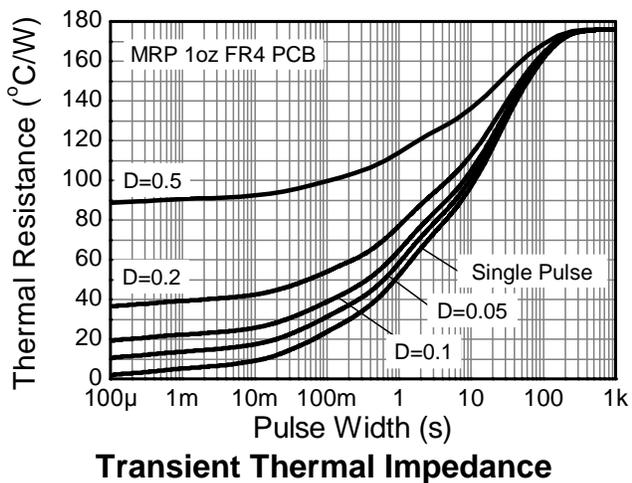
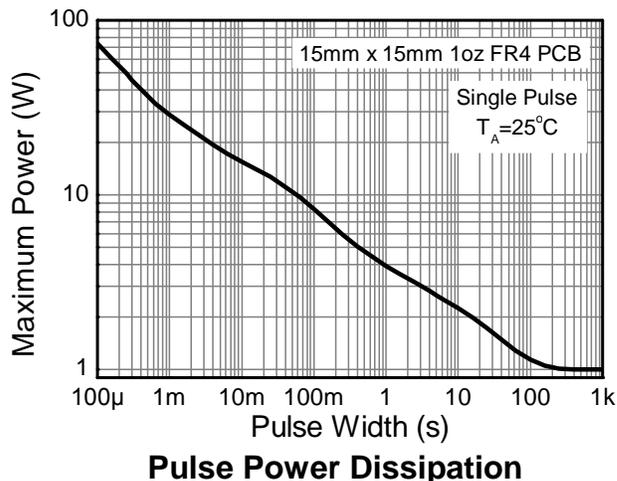
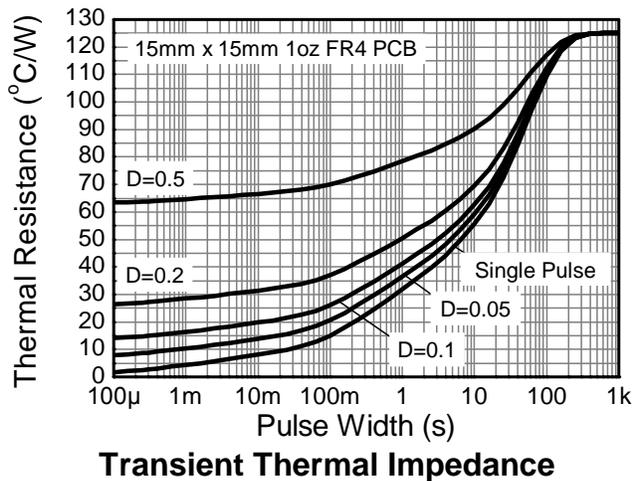
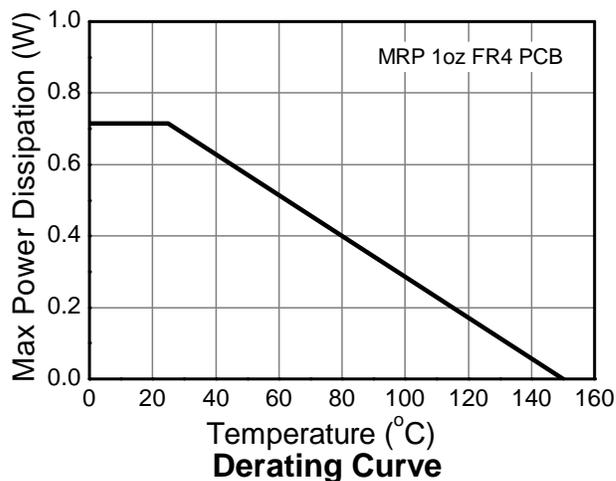
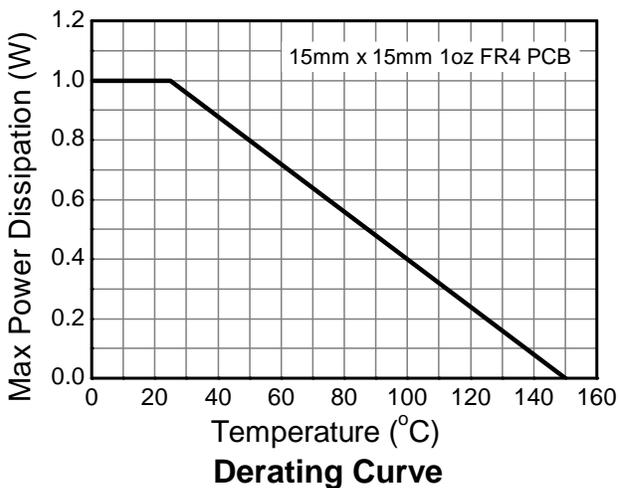
ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 6, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.
 - Same as Note 6, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
 - Same as Note 6, except the device is mounted with the exposed collector pad on 50mm x 50mm 1oz copper.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information


Thermal Characteristics and Derating Information (cont.)

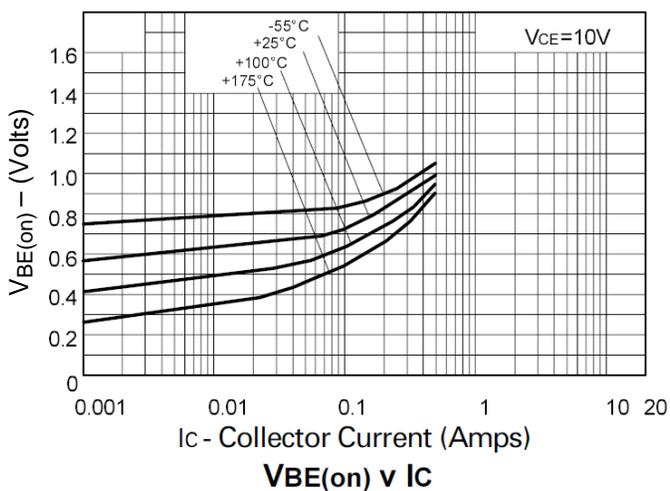
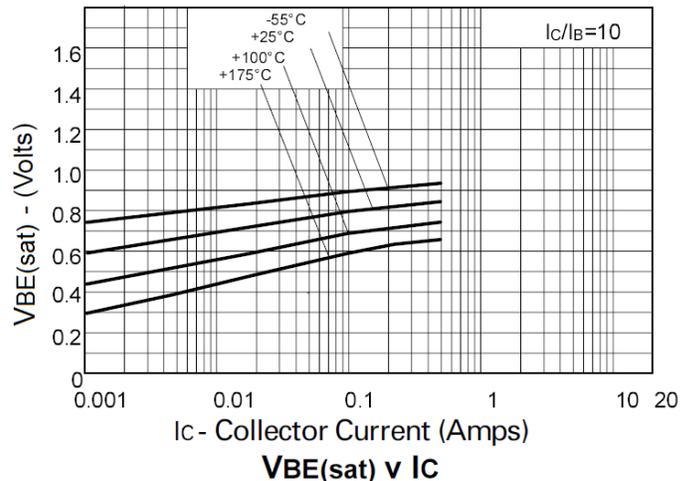
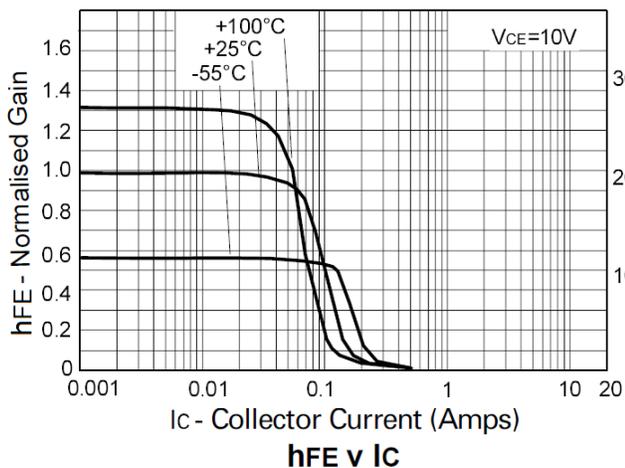
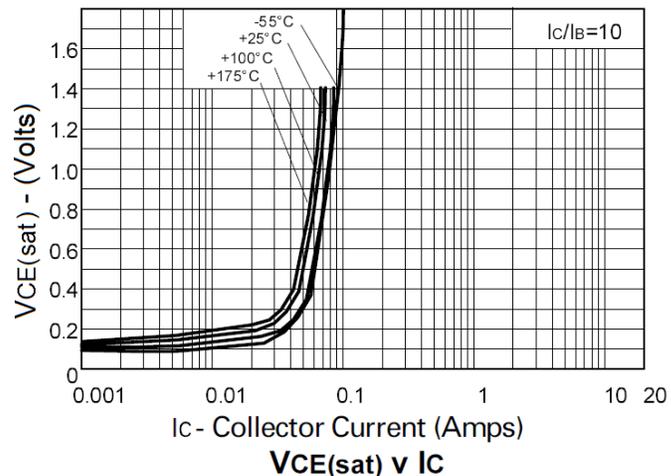
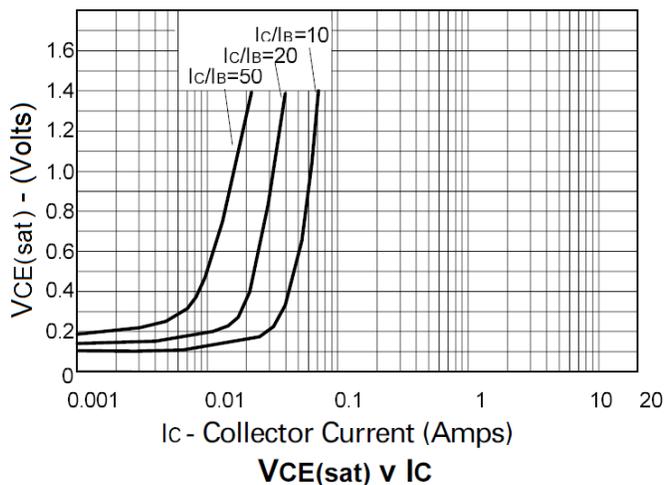


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	-400	-	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	-400	-	-	V	I _C = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-	-	V	I _E = -100μA
Collector Cutoff Current	I _{CB0}	-	<1	-100	nA	V _{CB} = -320V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5V
Emitter Cutoff Current	I _{CES}	-	<1	-100	nA	V _{CES} = -320V
DC Current Transfer Static Ratio (Note 12)	h _{FE}	100	-	-	-	I _C = -1mA, V _{CE} = -10V
		100	-	300		I _C = -50mA, V _{CE} = -10V
		15	-	-		I _C = -100mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	-	-	-0.2	V	I _C = -20mA, I _B = -2mA
		-	-	-0.5		I _C = -50mA, I _B = -6mA
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	-	-	-0.9	V	I _C = -50mA, I _B = -5mA
Base-Emitter Turn-on Voltage (Note 12)	V _{BE(on)}	-	-	-0.9	V	I _C = -50mA, V _{CE} = -10V
Transitional Frequency	f _T	50	-	-	MHz	I _E = -10mA, V _{CE} = -20V f = 20MHz
Output Capacitance	C _{obo}	-	-	5	pF	V _{CB} = -20V, f = 1MHz
Switching Time	t _{on}	-	95	-	ns	I _C = -50mA, V _C = -100V I _{B1} = -5mA, I _{B2} = 10mA
	t _{off}		1600			

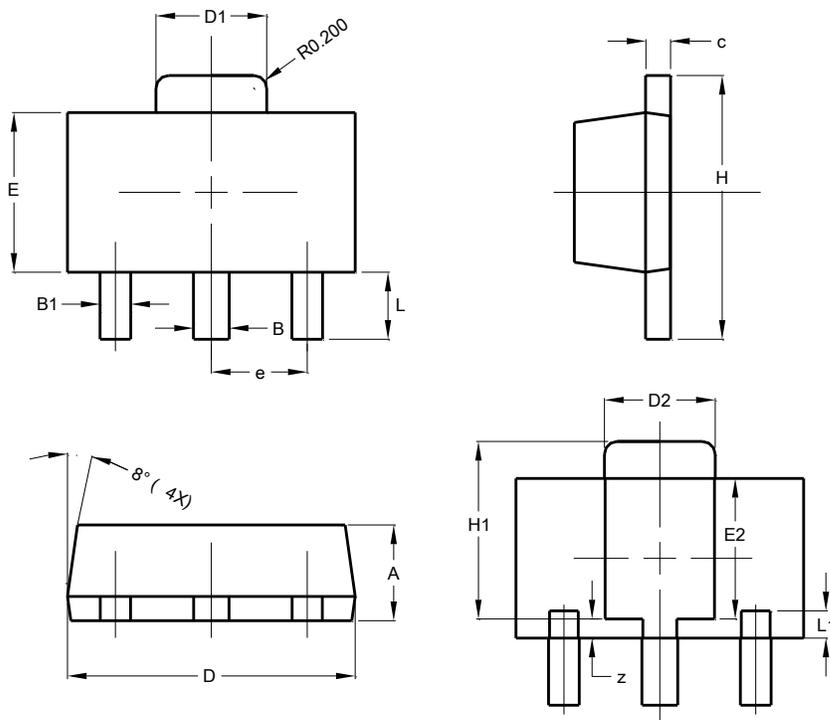
Note: 12. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

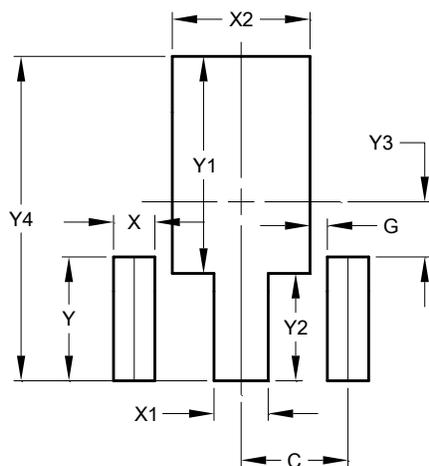
SOT89



SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.